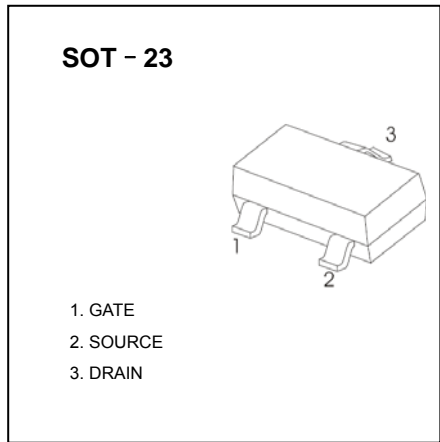
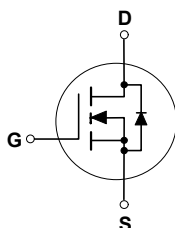
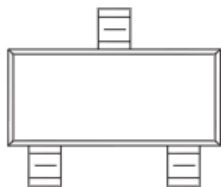


■ Features

- Simple Drive Requirement
- Small Package Outline
- Surface Mount Device



MARKING



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	3	A
		2.3	
Pulsed Drain Current *	I <sub>DM</sub>	10	
Power Dissipation	P <sub>D</sub>	1.38	W
Linear Derating Factor		0.01	W/°C
Thermal Resistance Junction-to-ambient	R <sub>thJa</sub>	90	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

\* 2. Pulse width ≤ 300us , duty cycle ≤ 2%.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			10	μA
		V <sub>DS</sub> =48, V <sub>GS</sub> =0V, T <sub>J</sub> =70°C			25	
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250μA	1		3	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A			90	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A			120	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =3A		5		S
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz		490	780	pF
Output Capacitance	C <sub>oss</sub>			55		
Reverse Transfer Capacitance	C <sub>rss</sub>			40		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =48V, I <sub>D</sub> =3A, V <sub>GS</sub> =4.5V		6	10	nC
Gate Source Charge	Q <sub>gs</sub>			1.6		
Gate Drain Charge	Q <sub>gd</sub>			3		
Turn-On DelayTime	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =1A RD=30Ω, R <sub>GEN</sub> =3.3Ω		6		ns
Turn-On Rise Time	t <sub>r</sub>			5		
Turn-Off DelayTime	t <sub>D(off)</sub>			16		
Turn-Off Fall Time	t <sub>f</sub>			3		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>S</sub> =3A, di/dt=100A/μs		25		
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>S</sub> =3A, di/dt=100A/μs		26		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.2A, V <sub>GS</sub> =0V			1.2	V

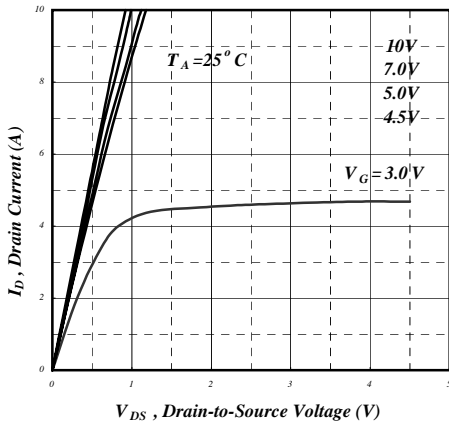


Fig 1. Typical Output Characteristics

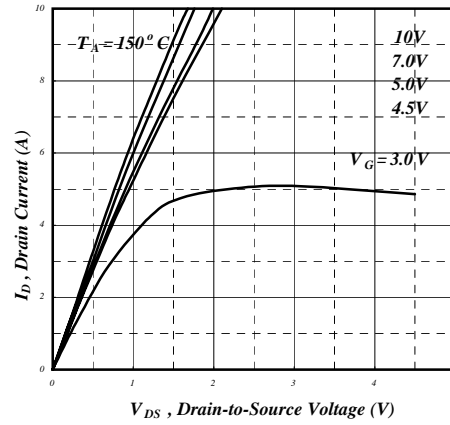


Fig 2. Typical Output Characteristics

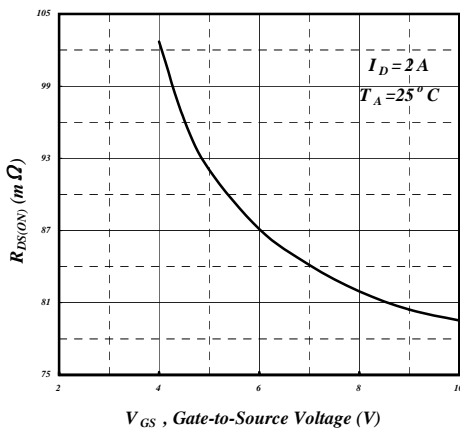


Fig 3. On-Resistance v.s. Gate Voltage

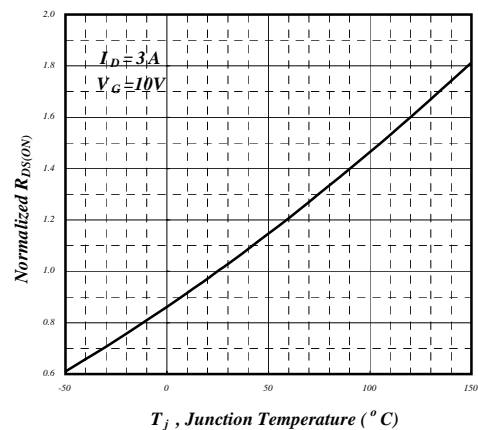


Fig 4. Normalized On-Resistance v.s. Junction Temperature

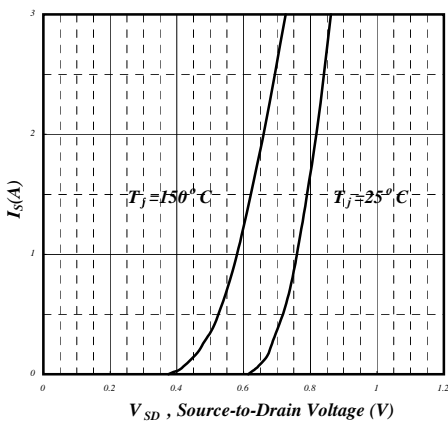


Fig 5. Forward Characteristic of Reverse Diode

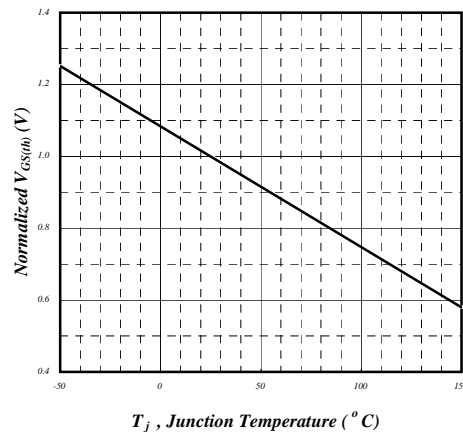


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

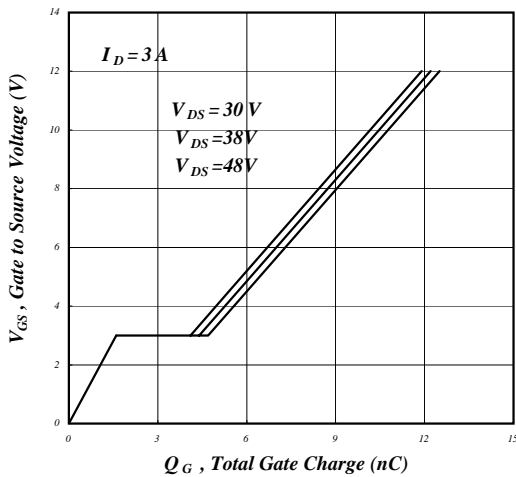


Fig 7. Gate Charge Characteristics

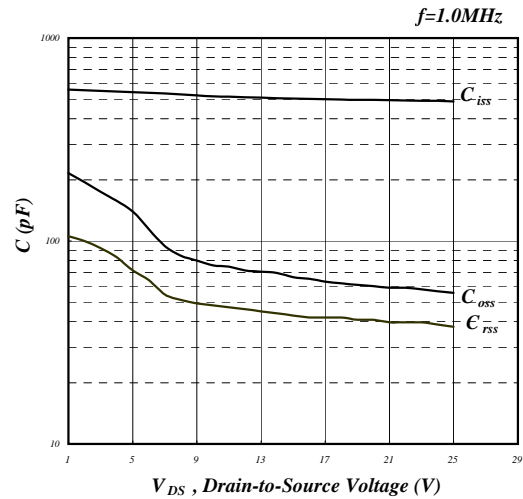


Fig 8. Typical Capacitance Characteristics

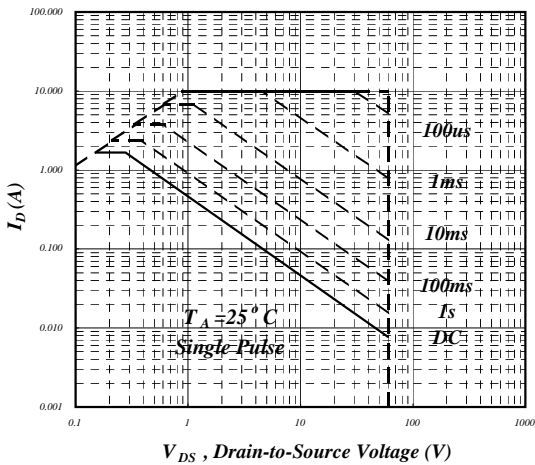


Fig 9. Maximum Safe Operating Area

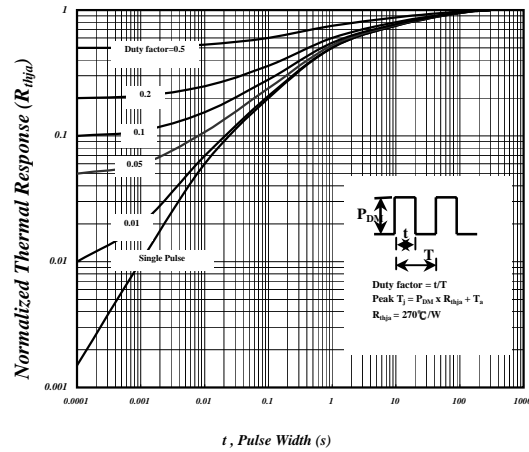


Fig 10. Effective Transient Thermal Impedance

单击下面可查看定价，库存，交付和生命周期等信息

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